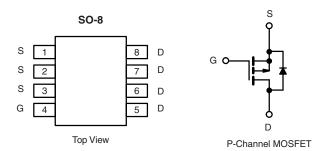


www.vishay.com

Vishay Siliconix

Automotive P-Channel 40 V (D-S) 150 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	- 40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.014			
$R_{DS(on)}$ (Ω) at V_{GS} = - 4.5 V	0.023			
I _D (A)	- 15.8			
Configuration	Single			



FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified
- 100 % Rq and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and Halogen-free	SQ4401DY-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unles		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 40		
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current ^a	T _C = 25 °C		- 15.8		
	T _C = 125 °C	- I _D	- 7.1		
Continuous Source Current (Diode Conduction) ^a		I _S	- 6.5	Α	
Pulsed Drain Current ^b		I _{DM}	- 63		
Single Pulse Avalanche Current	1 0.111	I _{AS}	- 30		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	45	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	-	6	10/	
	T _C = 125 °C	P_{D}	1.2	W	
Operating Junction and Storage Temperature	re Range	T _J , T _{stg}	- 55 to + 150	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	85	°C/W
unction-to-Foot (Drain)		R_{thJF}	21	C/ VV

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA		- 40	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		-	- 2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V _{DS} = - 40 V	-	-	- 1.0		
	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = - 40 V, T _J = 125 °C	-	-	- 50	μA	
		$V_{GS} = 0 V$	V _{DS} = - 40 V, T _J = 150 °C	-	-	- 120		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} ≥ - 5 V	- 30	-	-	Α	
Drain-Source On-State Resistance ^a		V _{GS} = - 10 V	I _D = - 10.5 A	-	0.011	0.014	Ω	
		V _{GS} = - 10 V	I _D = - 30 A, T _J = 125 °C	-	0.017	0.020		
	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 30 A, T _J = 150 °C	-	0.019	0.022		
		V _{GS} = - 4.5 V	I _D = - 30 A	-	0.017	0.023		
Forward Transconductanceb	9 _{fs}	V _{DS} = -	15 V, I _D = - 10.5 A	-	30	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}		_S = 0 V V _{DS} = - 20 V, f = 1 MHz	-	3400	4250	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	440	550		
Reverse Transfer Capacitance	C _{rss}			-	350	436		
Total Gate Charge ^c	Qg			-	74	115		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -20 \text{ V}, I_{D} = -10.5 \text{ A}$	-	11	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	16			
Gate Resistance	R _g	f = 1 MHz		1.16	-	3.21	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	58	85		
Rise Time ^c	t _r	V_{DD} = - 15 V, R_L = 15 Ω I_D \cong - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω		-	76	105	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	67	85		
Fall Time ^c	t _f			-	44	55		
Source-Drain Diode Ratings and Chara	icteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	- 63	Α	
Forward Voltage	V _{SD}	$I_F = -2.7 \text{ A}, V_{GS} = 0$			- 0.8	- 1.1	V	

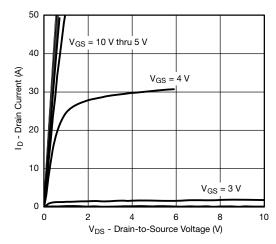
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

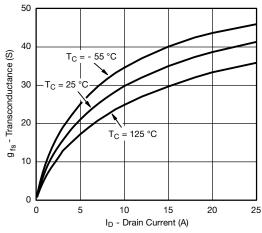
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



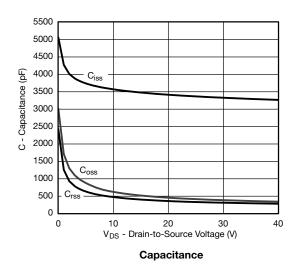
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

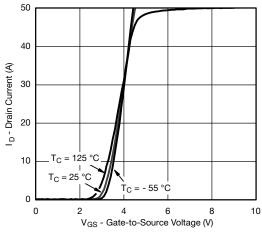


Output Characteristics

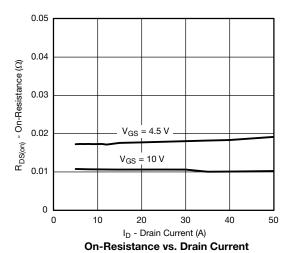


Transconductance



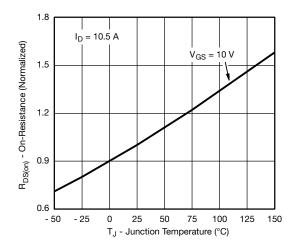


Transfer Characteristics

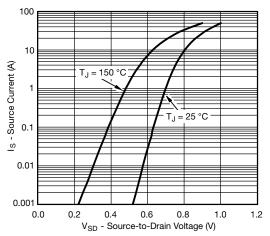




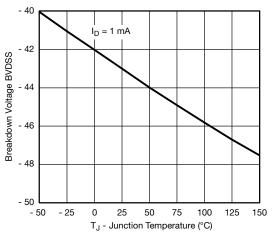
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



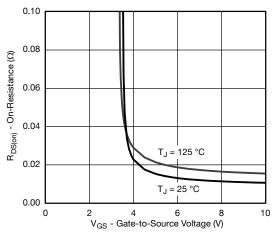
On-Resistance vs. Junction Temperature



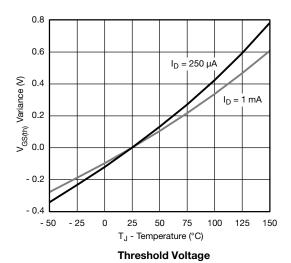
Source Drain Diode Forward Voltage



Breakdown Voltage BVDSS vs. Junction Temperature

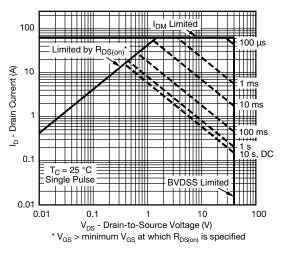


On-Resistance vs. Gate-to-Source Voltage

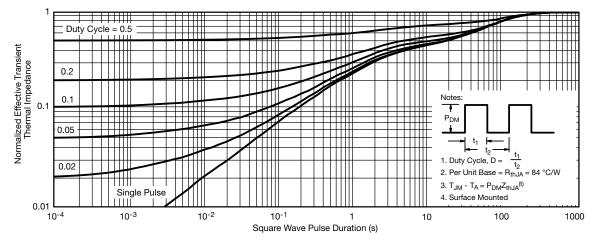




THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



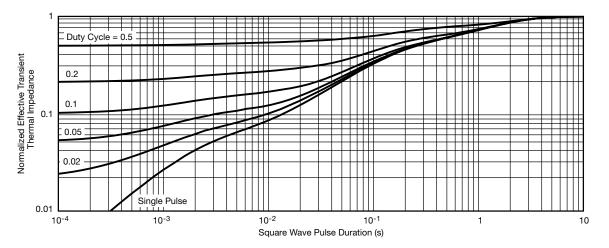
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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